

WE CLAIM:

claim 1
1. A method for forming a film comprising the steps of:

placing a substrate in a reaction chamber;
introducing a reactive gas into said reaction chamber;

inputting an energy for activating said reactive gas; and

depositing a silicon-containing compound on said substrate,

wherein said reactive gas comprises tetra-ethyl-oxy-silane.

2. The method of claim 1 wherein said energy is an electromagnetic energy.

3. The method of claim 1 wherein said energy is a photo energy.

claim 1 or 2
a 4. The method of claim 1 wherein said silicon compound is silicon oxide.

5. The method of claim 1 further comprising the steps of:

taking out said substrate from the reaction chamber after depositing said compound thereon;

introducing an etchant gas into said reaction chamber;

inputting an electromagnetic energy to said etchant gas so that said etchant gas is activated; and

etching said compound formed on an inside surface of said reaction chamber.

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6. The method of claim 1 wherein said etchant gas comprises NF_3 .

add
a2
add
c2
add D1
add E4
add F1